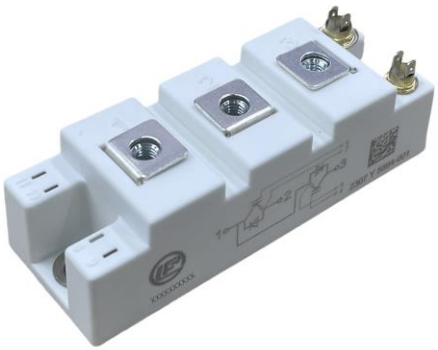
DFI75HF17DE1

1700V/75A Half Bridge IGBT Module

Description

The DFI75HF17DE1 offer lower losses and higher energy for soft switching applications.



Features

- 1700V75 A, VCE (sat)(typ.) = 2.40V
- Lower losses and higher energy
- Excellent short-circuit capability
- 34mm half bridge module

Applications

- Motor drive
- Inverter
- Power supply
- Wind Turbines

Circuit diagram

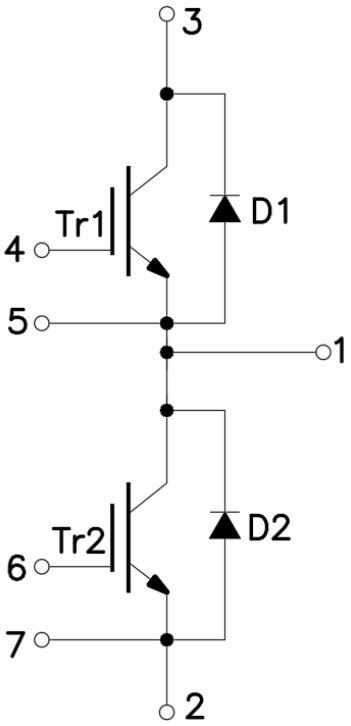


Figure 1. Out drawing & circuit diagram for DFI75HF17DE1

Pin Configuration and Marking Information

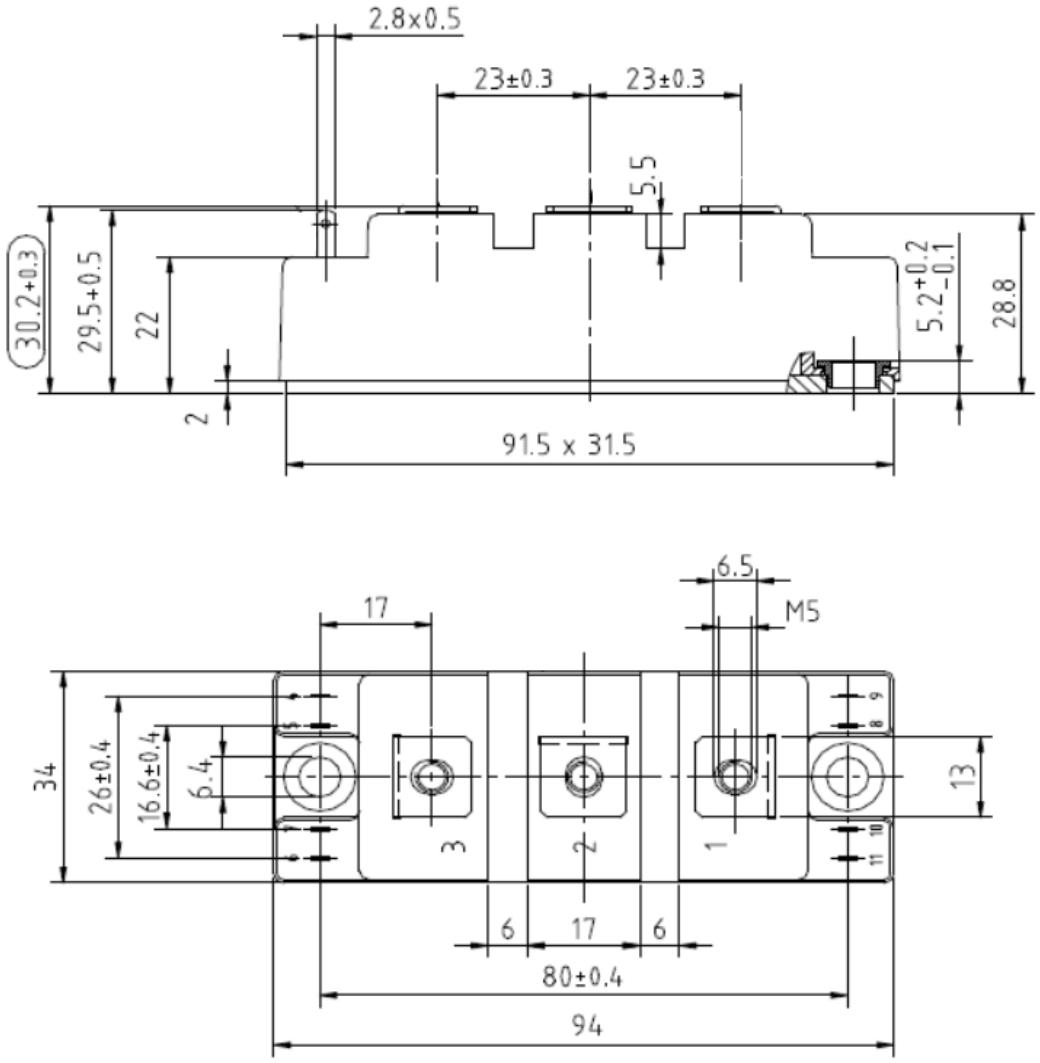


Figure 2. Pin configuration

Module

Parameter	Conditions	Value	Unit
Isolation Voltage	RMS, f = 50Hz, t =1min	2.5	KV
Material of module baseplate	-	Cu	-
Creepage distance	terminal to heatsink terminal to terminal	26 21	mm
Clearance	terminal to heatsink terminal to terminal	23.6 10	mm
CTI	-	>200	-
Module lead resistance, terminals – chip	T_C =25°C	0.8	mΩ
Mounting torque for module mounting	M5, M6	3 to 6	Nm
Weight	-	160	g

Maximum Ratings (IGBT, T_j =25°C unless otherwise specified)

Symbol	Parameter	Conditions	Ratings	Unit
V_{CES}	Collector-Emitter Voltage	G-E Short	1700	V
V_{GES}	Gate-Emitter Voltage	C-E Short	±30V	V
I_C	DC Continuous Collector Current	T_C =100°C	75	A
I_{CM}	Pulse Collector Current	t_p =1ms, Note1	150	A
P_C	Maximum Power Dissipation	T_C =25°C, T_j =150°C(IGBT)	450	W
T_{jop}	junction temperature	-	-40 to 150	°C
T_{stg}	Storage temperature	-	-40 to 125	°C

Note1: Pulse width limited by maximum junction temperature

Maximum Ratings (Freewheeling diode, T_j =25°C unless otherwise specified)

Symbol	Parameter	Conditions	Ratings	Unit
V_{RRM}	Peak Repetitive Revers Voltage	-	1700	V
I_F	Diode forward Current	- Tc =100°C	75	A
I_{FRM}	Repetitive peak forward Current	t_p =1ms, Note1	150	A
T_{jop}	junction temperature	-	-40 to 150	°C
T_{stg}	Storage temperature	-	-40 to 125	°C

Note1: Pulse width limited by maximum junction temperature

IGBT Electrical characteristics (T_j =25°C unless otherwise specified, chip)

Symbol	Item	Condition		Value			Unit
				Min.	Typ.	Max	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C =75A, V_{GE} =15V	T_j =25°C	-	2.40	-	V
			T_j =125°C	-	2.70	-	V
$V_{GE(th)}$	Gate-Emitter threshold Voltage	I_C =1mA, V_{CE} =V_{GE}		4.5	-	5.7	V
Q_G	Gate charge	V_{GE} = -15V to +15V		-	800	-	nC
R_{Gint}	Internal gate resistor	f=1M, Vpp=1V	T_j =25°C	-	5.6	-	Ω
C_{ies}	Input Capacitance	V_{CE} =25V, V_{GE} =0V, f =1MHz	T_j =25°C	-	6	-	nF
C_{oes}	Output Capacitance			-	0.8	-	nF
C_{res}	Reverse transfer Capacitance			-	0.5	-	nF
I_{CES}	Collector- Emitter Cut off Current	V_{CE} =1700V, V_{GE} =0V	T_j =25°C	-	-	5	mA
I_{GES}	Gate-Emitter Leakage Current	V_{GE} = ±30V, V_{CE} =0V	T_j =25°C	-	-	400	nA
$t_{d(on)}$	Turn-on delay time	V_{CC} = 900V, I_C = 75A, R_G = 6.2Ω, V_{GE} = ±15V, Inductive Load	T_j =25°C	-	140	-	ns
			T_j =125°C	-	150	-	
t_r	Rise time		T_j =25°C	-	50	-	ns
			T_j =125°C	-	45	-	
$t_{d(off)}$	Turn-off delay time		T_j =25°C	-	300	-	ns
			T_j =125°C	-	320	-	

t_f	Fall time	V_{CC} = 900V I_C = 75A R_G = 6.2Ω V_{GE} = ±15V Inductive Load	T_j =25°C	-	310	-	ns
			T_j=125°C	-	480	-	
E_{on}	Turn-on power dissipation		T_j =25°C	-	11	-	mJ
			T_j =125°C	-	14	-	
E_{off}	Turn-off power dissipation		T_j =25°C	-	9	-	mJ
			T_j =125°C	-	15	-	
$R_{th(j-c)}$	Thermal Resistance, Junction to Case (IGBT)			-		0.33	°C/W

Freewheeling Diode Electrical characteristics (T_j =25°C unless otherwise specified, chip)

Symbol	Item	Condition		Value			Unit
				Min.	Typ.	Max	
V_F	Diode Forward Voltage	I_F =75A, V_{GE} =0V	T_j =25°C	-	2.6	-	V
			T_j =125°C	-	2.75	-	
t_{rr}	Diode Reverse Recovery Time	I_F=75A, di/dt= 2100A/μs, V_R=900V, V_{GE} = -15V	T_j =25°C		90		nS
			T_j =125°C		200		
I_{rr}	Peak reverse recovery Current		T_j =25°C	-	80	-	A
			T_j =125°C	-	85	-	
Q_{rr}	Recovered charge		T_j=25°C	-	4	-	uC
			T_j =125°C	-	9	-	
E_{rr}	Reverse recovered energy		T_j =25°C	-	2.7	-	mJ
			T_j =125°C	-	4.2	-	
$R_{th(j-c)}$	Thermal Resistance, Junction to Case (Diode)			-		0.3	°C/W

Test Conditions

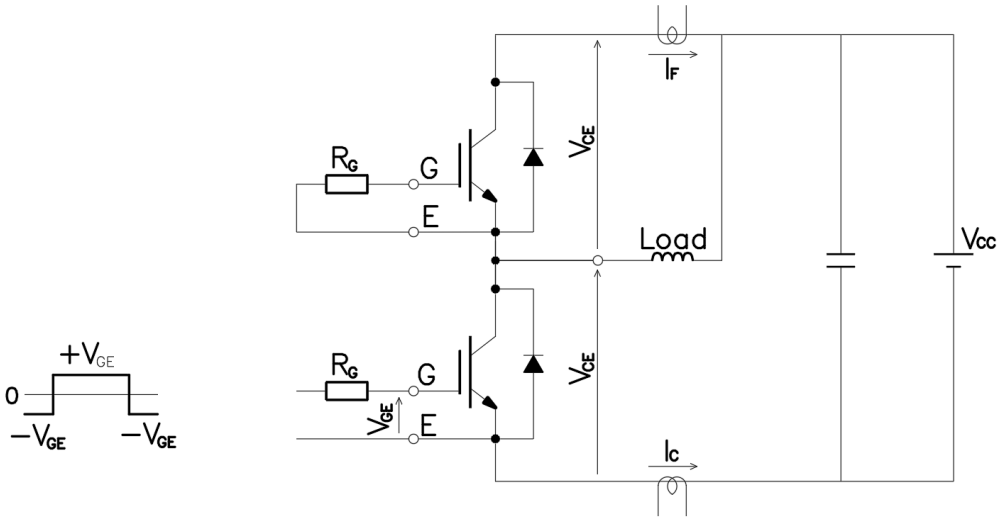


Figure 3. Switching time measure circuit

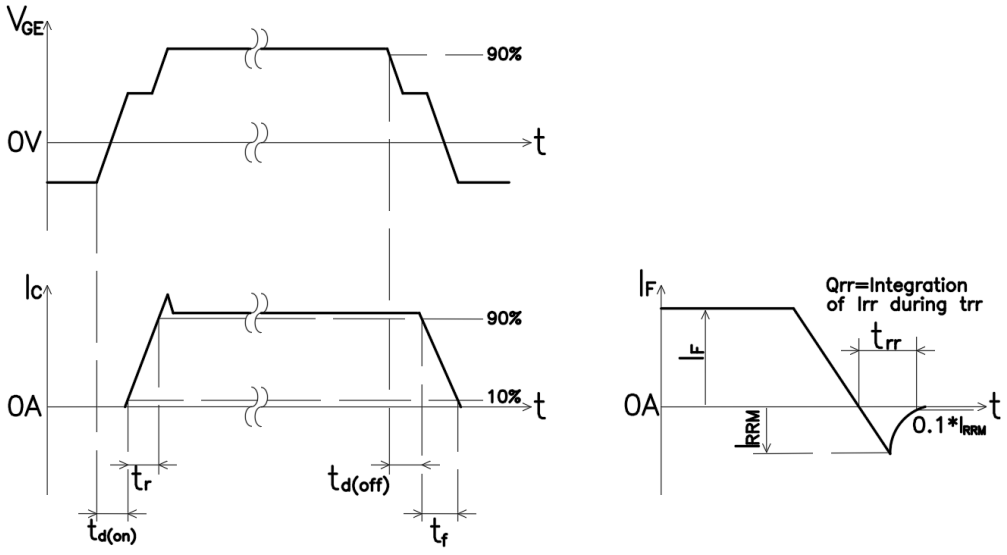


Figure 4. Switching time definition

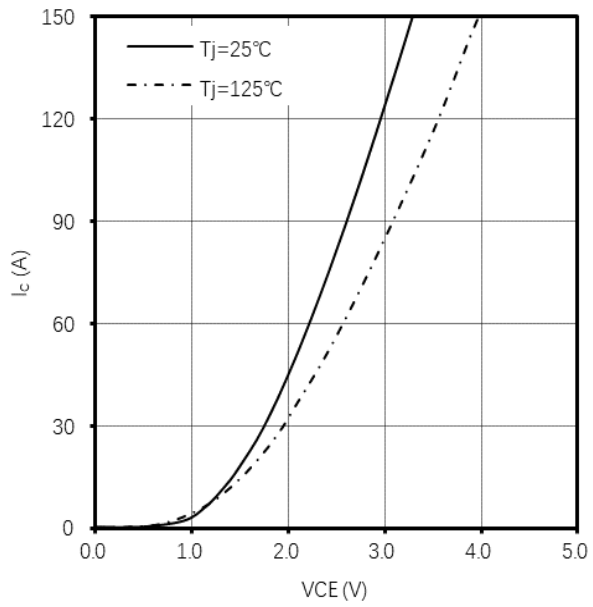


Figure 5. Ic vs V_{CE}
V_{GE} =15V

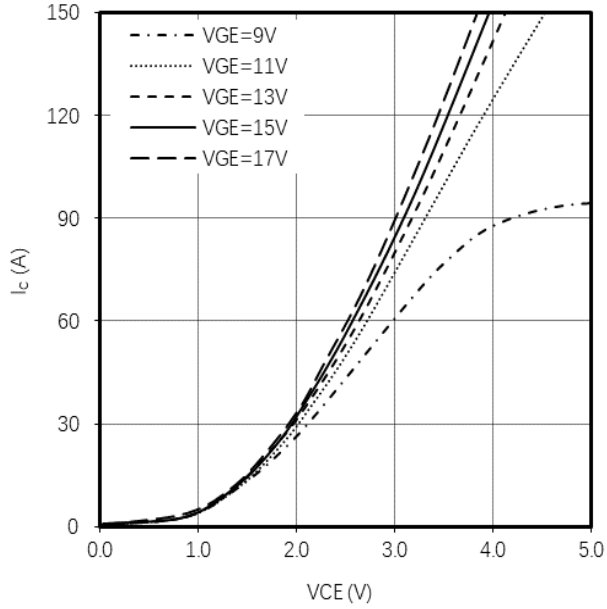


Figure 6. Ic vs V_{CE}
T_j =125°C

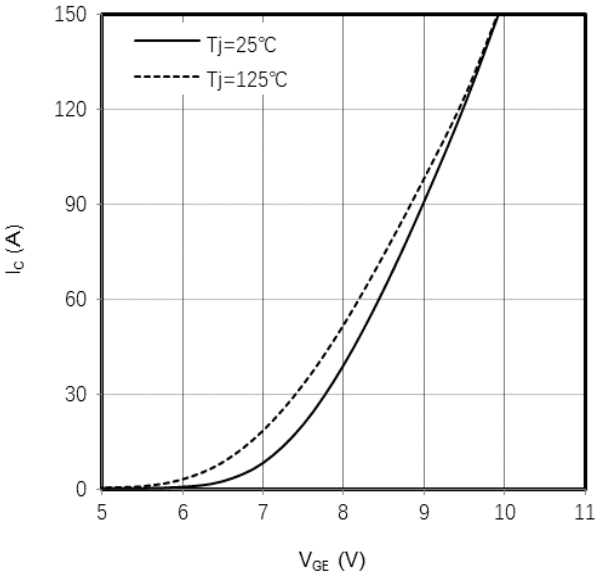


Figure 7. Ic vs V_{GE}
V_{CE} =20V

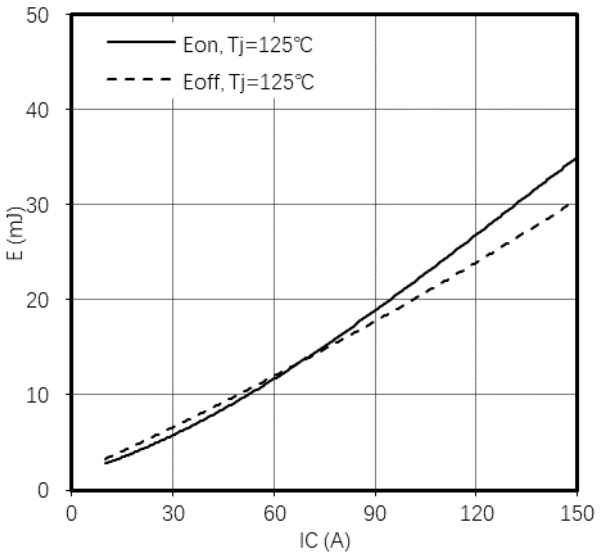


Figure8. E_{on}, E_{off} vs Ic(Typ)
V_{CC}=900V, V_{GE} =+15V/-15V, R_G =6.2Ω

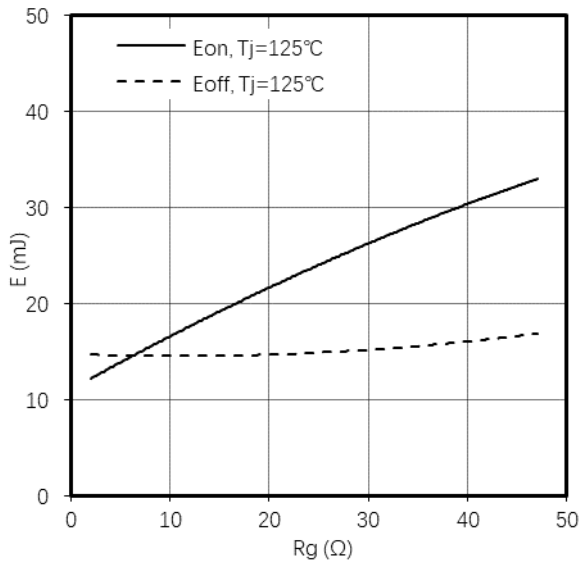


Figure 9. E_{on}, E_{off} vs R_g(Typ)
V_{CC} =900V, V_{GE} =+15V/-15V, I_C =75A

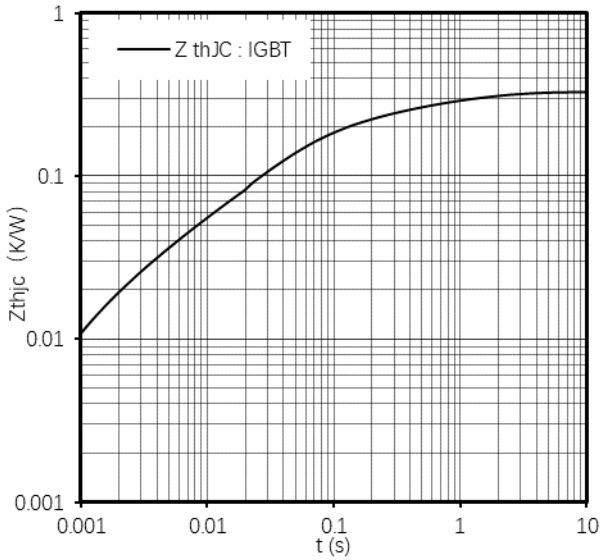


Figure 10. Transient thermal impedance IGBT , Zthjc=f(t)

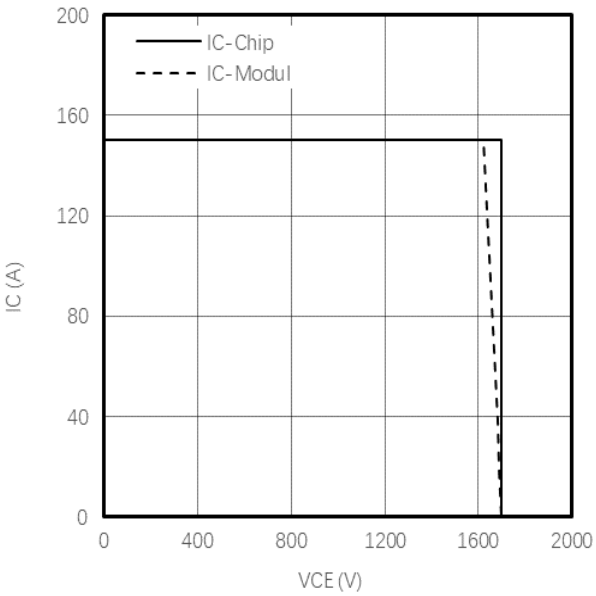


Figure 11. Reverse bias safe operating area IGBT, I_C=f(V_{CE}),V_{GE}=±15V,R_{Goff}=6.2Ω，Tvj=125℃

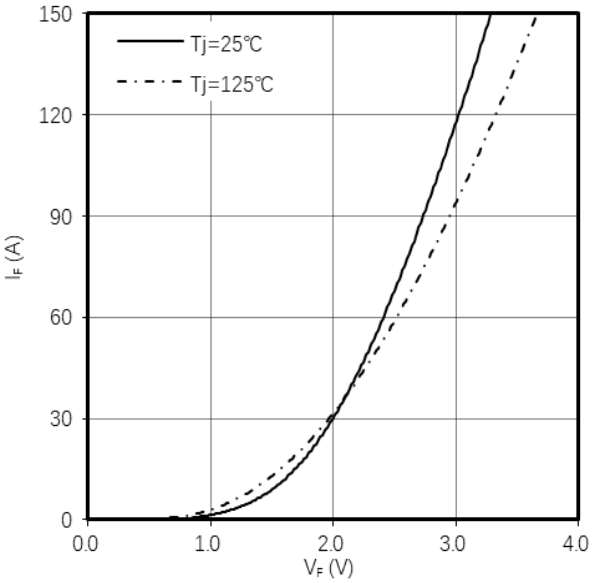


Figure 12. Forward characteristic of Diode ， I_F=f(V_F)

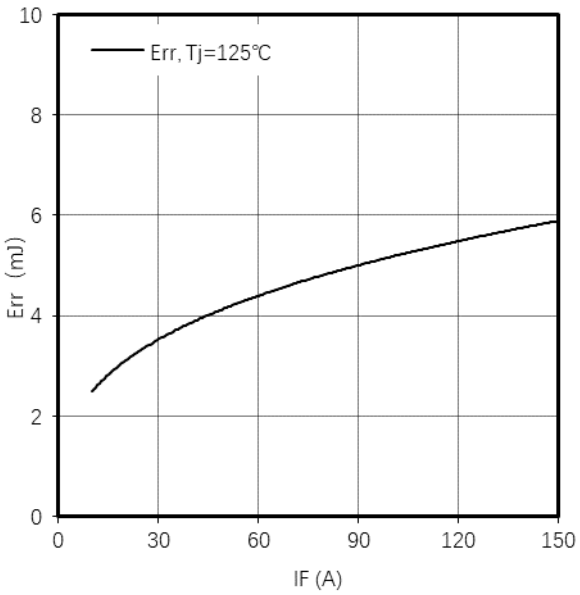


Figure 13. Switching losses Diode, $E_{rr}=f(I_F)$,,$R_{Gon}=6.2\Omega$,$V_{CE}=900V$

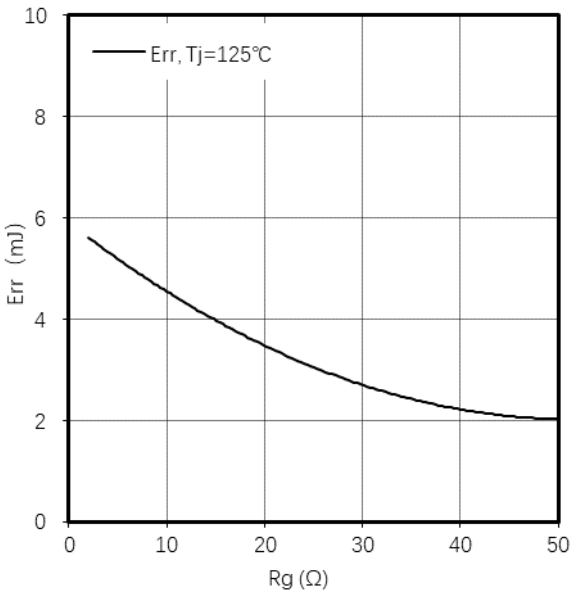


Figure 14. Switching losses Diode, $E_{rr}=f(R_G)$,$I_F=75A$,$V_{CE}=900V$

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